





DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

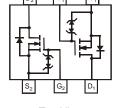
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- ESD Protected up to 2KV
- "Green" Device (Note 2)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.015 grams (approximate)







Top View

Top View Internal Schematic

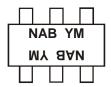
Ordering Information (Note 3)

Part Number	Case	Packaging
DMN2004DMK-7	SOT26	3000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



NAB = Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	Т	U	V	W	Χ	Υ	Z	Α	В	С	D	Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code				4	-	^	_	0	0		N I	7



Maximum Ratings @T_A = 25°C unless otherwise specified

	Characteristic		Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±8	V
Drain Current (Note 4)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I _D	540 390	mA
Pulsed Drain Current (Note 5)			I _{DM}	1.5	Α

Thermal Characteristics $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P_{D}	225	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	556	°C/W
Operating and Storage Temperature Range	$T_{J_{I}}T_{STG}$	-65 to +150	°C

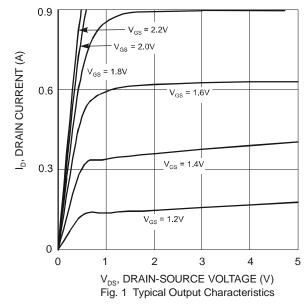
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					•	
Drain-Source Breakdown Voltage	BV _{DSS}	20		_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}			1	μΑ	$V_{DS} = 16V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}			±1	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	0.5		1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
	R _{DS (ON)}	_	0.4 0.5 0.7	0.55 0.70 0.9	Ω	$V_{GS} = 4.5V, I_D = 540mA$
Static Drain-Source On-Resistance						$V_{GS} = 2.5V, I_D = 500mA$
						$V_{GS} = 1.8V, I_D = 350mA$
Forward Transfer Admittance	Y _{fs}	200		_	ms	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage (Note 6)	V _{SD}	0.5	_	1.4	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}			150	pF	V 40V V 0V
Output Capacitance	Coss			25	pF	$V_{DS} = 16V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		_	20	pF	1 = 1.0IVII IZ

Notes:

- 4. Device mounted on FR-4 PCB.
- 5. Pulse width ≤10μS, Duty Cycle ≤1%.
- 6. Short duration pulse test used to minimize self-heating effect.





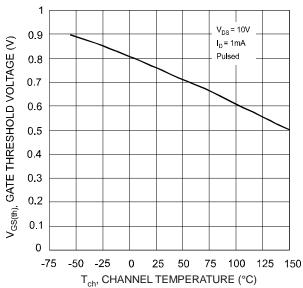


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

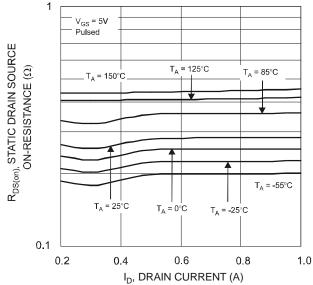


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

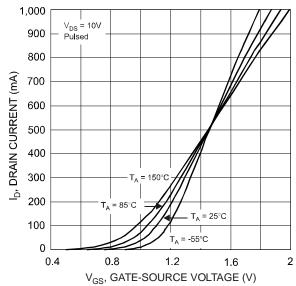


Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

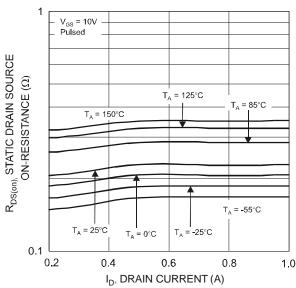
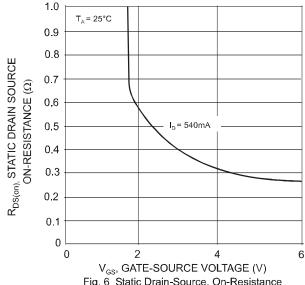


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current





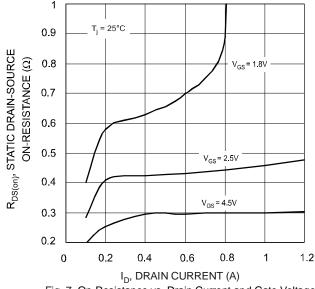
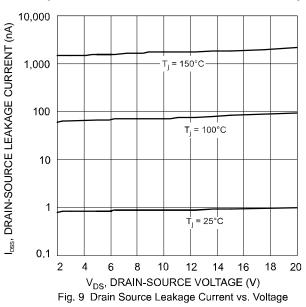


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage



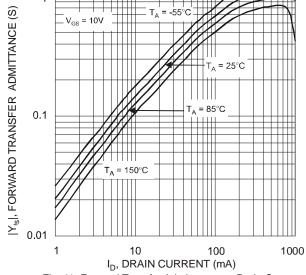


Fig. 11 Forward Transfer Admittance vs. Drain Current

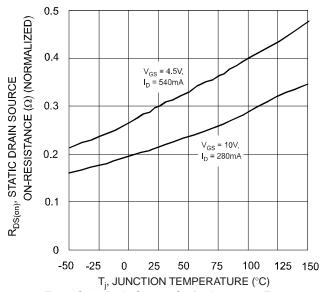


Fig. 8 Static Drain-Source, On-Resistance vs. Temperature

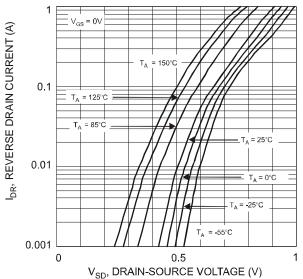
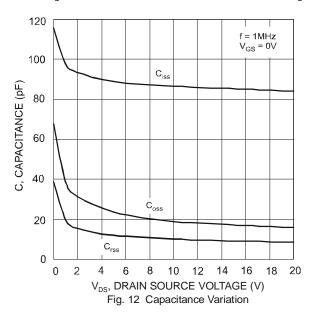
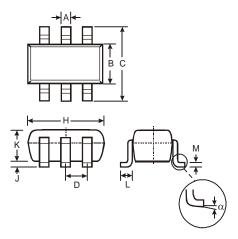


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage



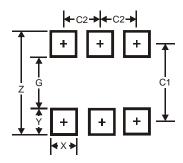


Package Outline Dimensions



	SOT26							
Dim	Min	Max	Тур					
Α	0.35	0.50	0.38					
В	1.50	1.70	1.60					
С	2.70	3.00	2.80					
D	_	_	0.95					
Н	2.90	3.10	3.00					
J	0.013	0.10	0.05					
K	1.00	1.30	1.10					
L	0.35	0.55	0.40					
M	0.10	0.20	0.15					
α	0°	8°	_					
All D	All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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